# ST(意法) STTH30W02CW PDF



# 深圳创唯电子有限公司

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## STTH30W02C

## Turbo 2 ultrafast high voltage rectifier

#### Datasheet - production data

#### **Features**

- Ultrafast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses
- ECOPACK<sup>®</sup>2 compliant component

### **Description**

The STTH30W02CW, uses ST Turbo 2, 200 V technology. It is especially suited to be used for DC/DC and DC/AC converters in secondary stage of MIG/MMA/TIG welding machine. Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.

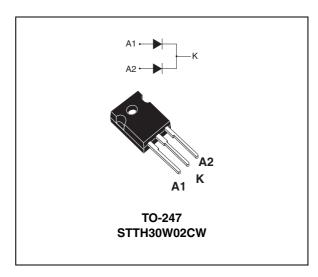


Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	2 x 15 A
V <sub>RRM</sub>	200 V
t <sub>rr</sub> (typ)	20 ns
T <sub>j</sub> (max)	175 °C
V <sub>F</sub> (typ)	0.90 V

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## 1 Characteristics

Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified)

Symbol	Paramete	Value	Unit			
$V_{RRM}$	Repetitive peak reverse voltage			200	V	
I <sub>F(RMS)</sub>	Forward rms current			30	Α	
I <sub>F(AV)</sub> Average fo	Average forward current, $\delta = 0.5$	T <sub>c</sub> = 125 °C	Per diode	15	Α	
	Average lorward current, $\delta = 0.5$	T <sub>c</sub> = 115°C	Per device	30	Α	
I <sub>FSM</sub>	Surge non repetitive forward current   t <sub>p</sub> = 10 ms sinusoidal			140	Α	
T <sub>stg</sub>	Storage temperature range	-65 to + 175	°C			
T <sub>j</sub>	Maximum operating junction temperation	+ 175	°C			

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit	
В	Junction to case	Per diode	2.5	
R <sub>th(j-c)</sub>	Total	Total	1.5	°C / W
R <sub>th(c)</sub>	Coupling		0.5	

When diodes 1 and 2 are used simultaneously:

 $T_{j}(diode 1) = P(diode 1) \times R_{th(j-c)}(per diode) + P(diode 2) \times R_{th(c)}$ 

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I <sub>R</sub> <sup>(1)</sup> Reverse leakage currer	Payaraa laakaga aurrant	$T_j = 25  ^{\circ}C$	$V_R = V_{RRM}$			10	μΑ
	neverse leakage current	T <sub>j</sub> = 125 °C			5	50	
	V (2) Famurard valtage dues	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 15A			1.20	
V <sub>F</sub> <sup>(2)</sup>		T <sub>j</sub> = 150 °C			0.90	1.05	V
V <sub>F</sub> · · · · · · · · · · · · · · · · · · ·	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 30 A			1.4	V
		T <sub>j</sub> = 150 °C			1.1	1.3	

<sup>1.</sup> Pulse test:  $t_p = 5$  ms,  $\delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 0.8 \text{ x } I_{F(AV)} + 0.0167 I_{F(RMS)}^{2}$$

<sup>2.</sup> Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2%

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Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions			Тур	Max.	Unit
I <sub>RM</sub>	Reverse recovery current		15 4 1/ 100 1/		7	9	Α
Q <sub>RR</sub>	Reverse recovery charge	T <sub>j</sub> = 125 °C	$I_F = 15 \text{ A}, V_R = 160 \text{ V}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$		160		nC
S <sub>factor</sub>	Softness factor				0.3		
t <sub>rr</sub>	Reverse recovery time	T <sub>j</sub> = 25 °C	$I_F = 1 \text{ A}, V_R = 30 \text{ V}$ $dI_F/dt = -100 \text{ A/}\mu\text{s}$		20	25	ns
t <sub>fr</sub>	Forward recovery time	T <sub>j</sub> = 25 °C	$T_j = 25 ^{\circ}\text{C}$ $I_F = 15 \text{A},  V_{FR} = 1.1 \text{V}$			200	ns
V <sub>FP</sub>	Forward recovery voltage	T <sub>j</sub> = 25 °C	dI <sub>F</sub> /dt = 100 A/μs		1.6	2.4	V

Figure 1. Average forward power dissipation Figure 2. Forward voltage drop versus versus average forward current (per diode) forward current (per diode)

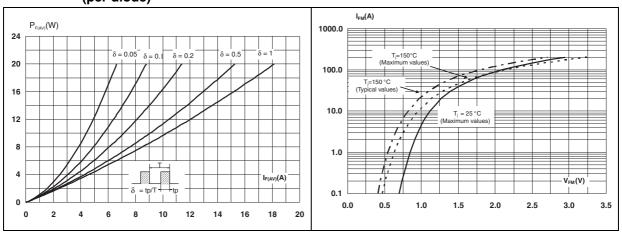


Figure 4.

Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Peak reverse recovery current

versus dl<sub>F</sub>/dt (typical values, per

 $Z_{th(j-c)}/R_{th(j-c)}$ 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 0.0 1.E-04 1.E-03 1.E-02 1.E-01 1.E+00

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Figure 5. Reverse recovery time versus dl<sub>F</sub>/dt Figure 6. Reverse recovery charges versus (typical values, per diode) dl<sub>F</sub>/dt (typical values, per diode)

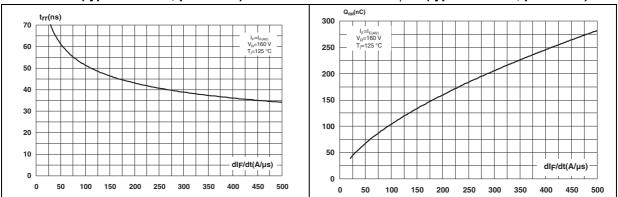


Figure 7. Relative variations of dynamic parameters versus junction temperature

Figure 8. Reverse recovery softness factor versus dl<sub>F</sub>/dt (typical values, per diode)

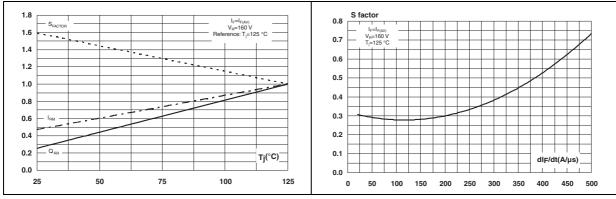
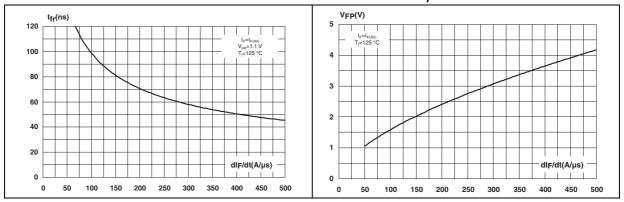


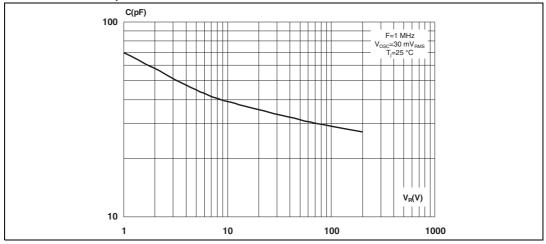
Figure 9. Forward recovery time versus dl<sub>F</sub>/dt Figure 10. Transient peak forward voltage (typical values, per diode)

Transient peak forward voltage versus dl<sub>F</sub>/dt (typical values, per diode)



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Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



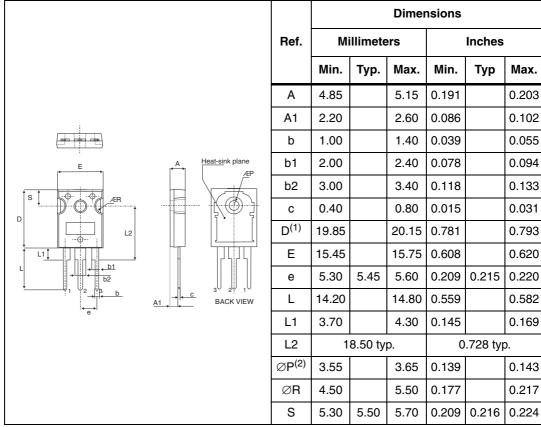
Package information STTH30W02C

## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m (1.0 N·m maximum)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Table 6. TO-247 dimensions



- 1. Dimension D plus gate protrusion does not exceed 20.5 mm
- 2. Resin thickness around the mounting hole is not less than 0.9 mm

# **3** Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH30W02CW	STTH30W02CW	TO-247	4.46 g	50	Tube

## 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
05-Oct-2012	1	First issue.

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